



July 2007

FDS9958

Dual P-Channel PowerTrench[®] MOSFET

-60V, -2.9A, 105mΩ

Features

- Max $r_{DS(on)}$ = 105mΩ at $V_{GS} = -10V, I_D = -2.9A$
- Max $r_{DS(on)}$ = 135mΩ at $V_{GS} = -4.5V, I_D = -2.5A$
- RoHS Compliant



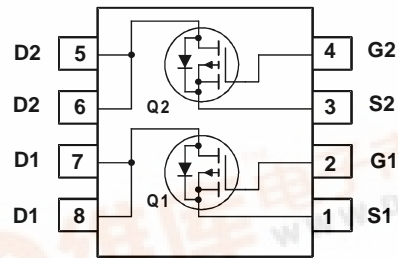
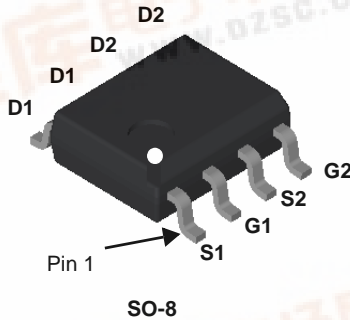
General Description

These P-channel logic level specified MOSFETs are produced using Fairchild Semiconductor's advanced PowerTrench[®] process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

These devices are well suited for portable electronics applications: load switching and power management, battery charging and protection circuits.

Applications

- Load Switch
- Power Management



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	-60	V
V_{GS}	Gate to Source Voltage	± 20	V
I_D	Drain Current -Continuous	(Note 1a) -2.9	A
	-Pulsed	-12	
E_{AS}	Single Pulse Avalanche Energy	(Note 3) 54	mJ
P_D	Power Dissipation for Dual Operation	2	W
	Power Dissipation	(Note 1a) 1.6	
	Power Dissipation	(Note 1b) 0.9	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	40	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a) 78	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDS9958	FDS9958	SO-8	330mm	12mm	2500units

FDS9958 Dual P-Channel PowerTrench[®] MOSFET

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = -250\mu\text{A}, V_{GS} = 0\text{V}$	-60			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\mu\text{A}$, referenced to 25°C		-52		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -48\text{V}, V_{GS} = 0\text{V}, T_J = 125^\circ\text{C}$			-1 -100	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$			± 100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = -250\mu\text{A}$	-1.0	-1.6	-3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = -250\mu\text{A}$, referenced to 25°C		4		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = -10\text{V}, I_D = -2.9\text{A}$		82	105	m Ω
		$V_{GS} = -4.5\text{V}, I_D = -2.5\text{A}$		103	135	
		$V_{GS} = -10\text{V}, I_D = -2.9\text{A}, T_J = 125^\circ\text{C}$		131	190	
g_{FS}	Forward Transconductance	$V_{DD} = -5\text{V}, I_D = -2.9\text{A}$		7.7		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = -30\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$		765	1020	pF
C_{oss}	Output Capacitance			90	120	pF
C_{rss}	Reverse Transfer Capacitance			40	65	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -30\text{V}, I_D = -2.9\text{A}, V_{GS} = -10\text{V}, R_{GEN} = 6\Omega$		6	12	ns
t_r	Rise Time			3	10	ns
$t_{d(off)}$	Turn-Off Delay Time			27	43	ns
t_f	Fall Time			6	12	ns
Q_g	Total Gate Charge		$V_{GS} = 0\text{V to } -10\text{V}$		16	23
Q_g	Total Gate Charge	$V_{GS} = 0\text{V to } -4.5\text{V}$		8	12	nC
Q_{gs}	Gate to Source Charge	$V_{DD} = -30\text{V}, I_D = -2.9\text{A}$		2		nC
Q_{gd}	Gate to Drain "Miller" Charge			3		nC

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = -1.3\text{A}$ (Note 2)		-0.8	-1.2	V
t_{rr}	Reverse Recovery Time	$I_F = -2.9\text{A}, di/dt = 100\text{A}/\mu\text{s}$		26	42	ns
Q_{rr}	Reverse Recovery Charge			21	35	nC

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a 1in^2 pad 2 oz copper pad on a $1.5 \times 1.5\text{in.}$ board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) $78^\circ\text{C}/\text{W}$ when mounted on a 1in^2 pad of 2 oz copper



b) $135^\circ\text{C}/\text{W}$ when mounted on a minimum pad

2. Pulse Test: Pulse Width < $300\mu\text{s}$, Duty cycle < 2.0%.

3. UIL condition: Starting $T_J = 25^\circ\text{C}$, $L = 3\text{mH}$, $I_{AS} = 6\text{A}$, $V_{DD} = 60\text{V}$, $V_{GS} = 10\text{V}$.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

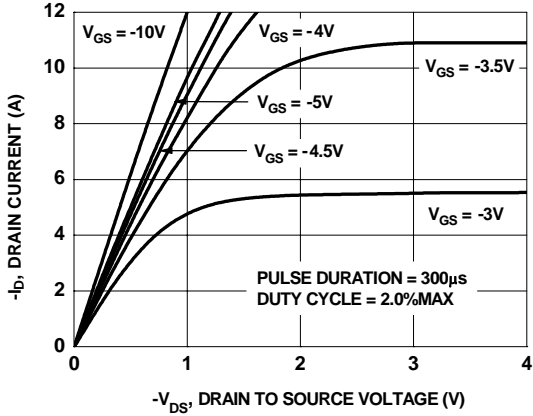


Figure 1. On-Region Characteristics

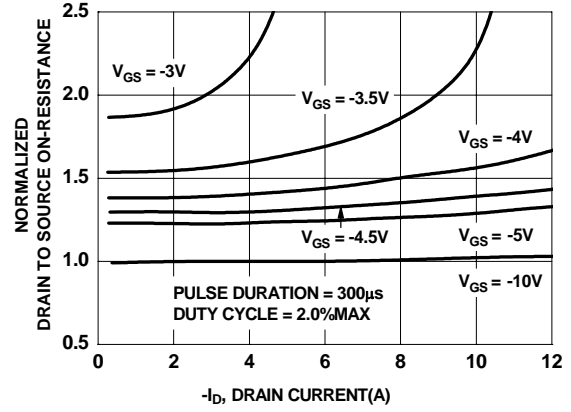


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

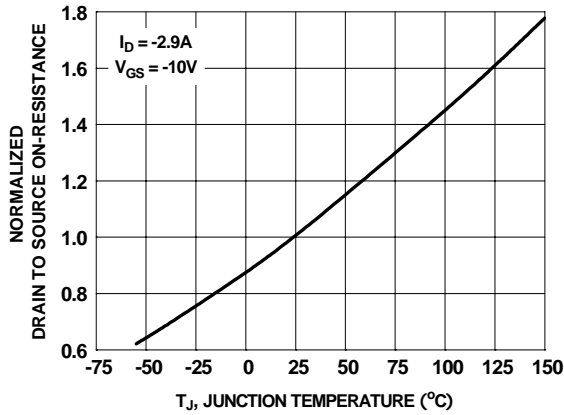


Figure 3. Normalized On-Resistance vs Junction Temperature

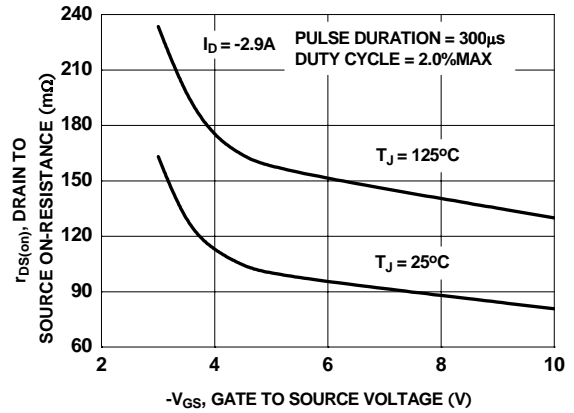


Figure 4. On-Resistance vs Gate to Source Voltage

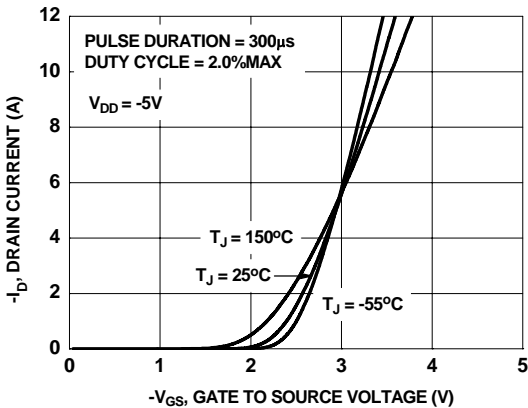


Figure 5. Transfer Characteristics

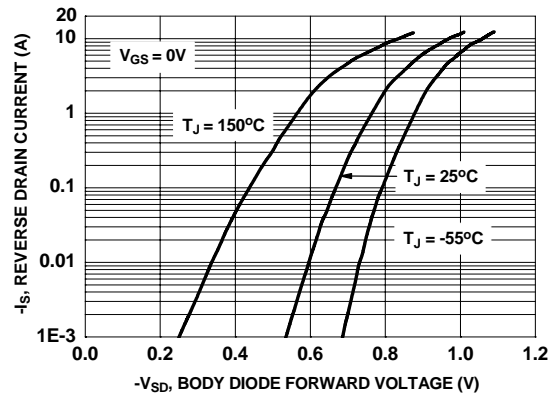


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

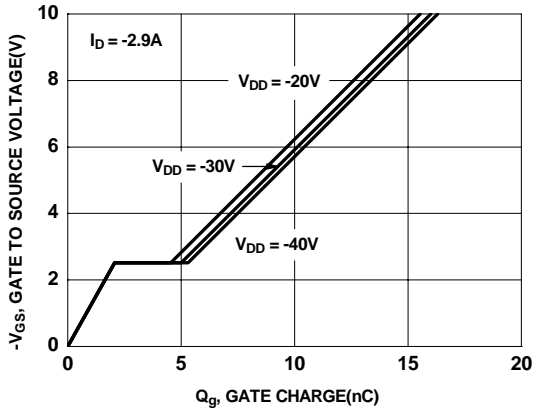


Figure 7. Gate Charge Characteristics

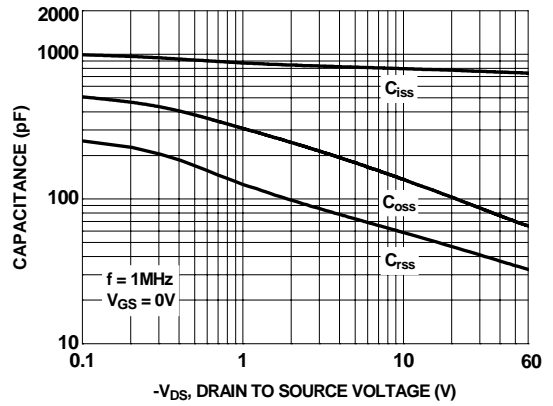


Figure 8. Capacitance vs Drain to Source Voltage

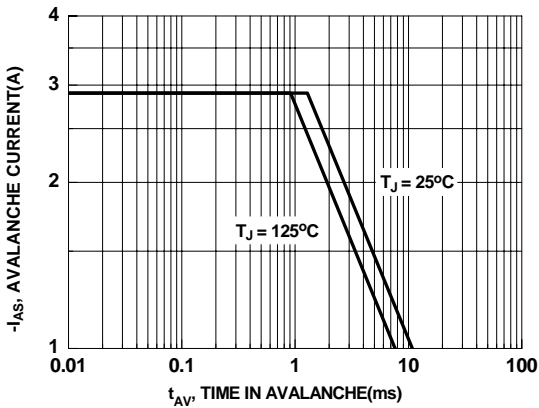


Figure 9. Unclamped Inductive Switching Capability

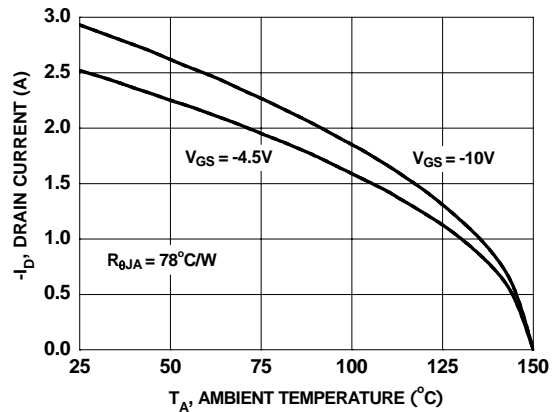


Figure 10. Maximum Continuous Drain Current vs Ambient Temperature

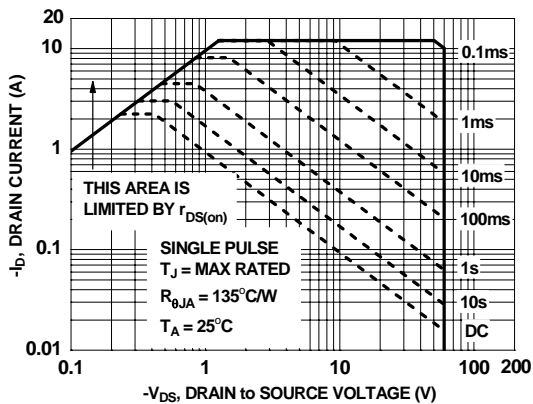


Figure 11. Forward Bias Safe Operating Area

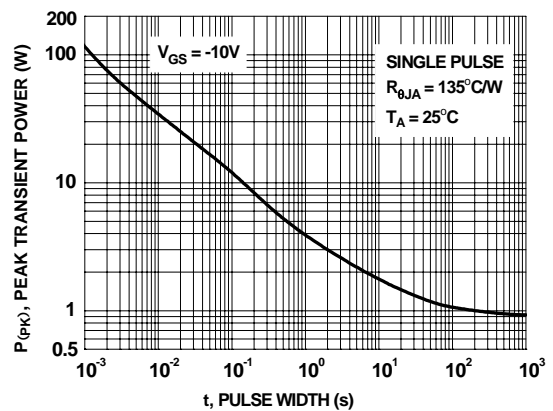


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

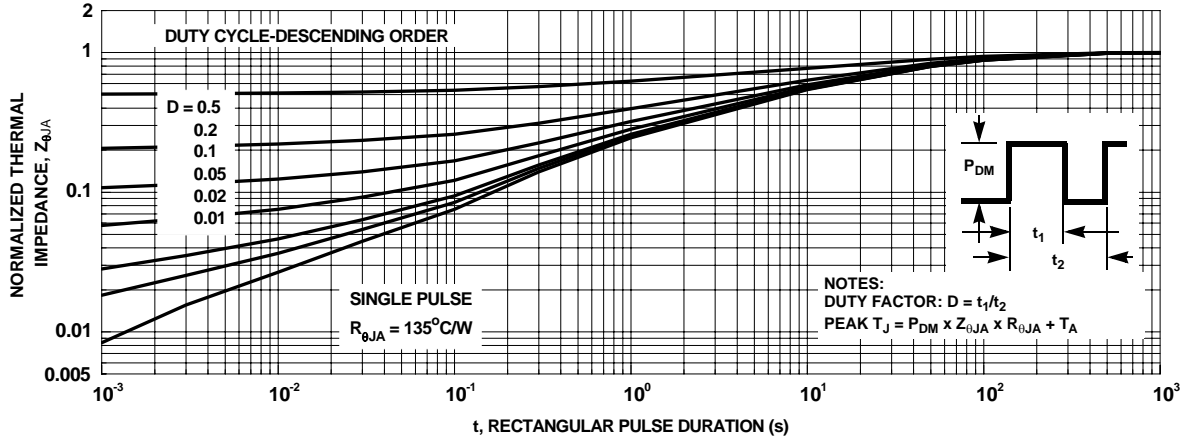



Figure 13. Transient Thermal Response Curve



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